

查询"2SA1160"供应商 TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1160

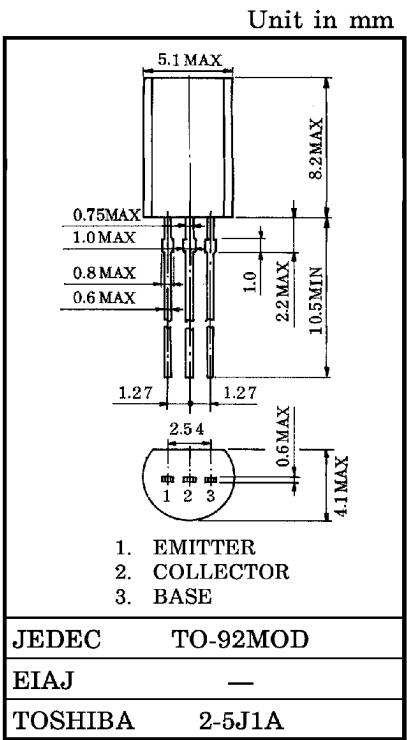
STROBE FLASH APPLICATIONS.  
MEDIUM POWER AMPLIFIER APPLICATIONS.

- High DC Current Gain and Excellent  $h_{FE}$  Linearity
  - :  $h_{FE(1)} = 140 \sim 600$  ( $V_{CE} = -1V$ ,  $I_C = -0.5A$ )
  - :  $h_{FE(2)} = 60$  (Min.), 120 (Typ.) ( $V_{CE} = -1V$ ,  $I_C = -4A$ )
- Low Saturation Voltage
  - :  $V_{CE(sat)} = -0.5V$  (Max.) ( $I_C = -2A$ ,  $I_B = -50mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	-20	V
Collector-Emitter Voltage		$V_{CEO}$	-10	V
Emitter-Base Voltage		$V_{EBO}$	-6	V
Collector Current	DC	$I_C$	-2	A
	Pulsed (Note 1)	$I_{CP}$	-4	
Base Current		$I_B$	-2	A
Collector Power Dissipation		$P_C$	900	mW
Junction Temperature		$T_j$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ C$

Note 1 : Pulse Width=10ms (Max.), Duty Cycle=30% (Max.)



Weight : 0.36g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

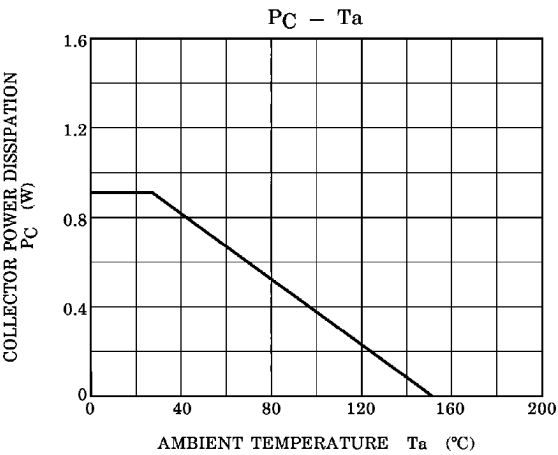
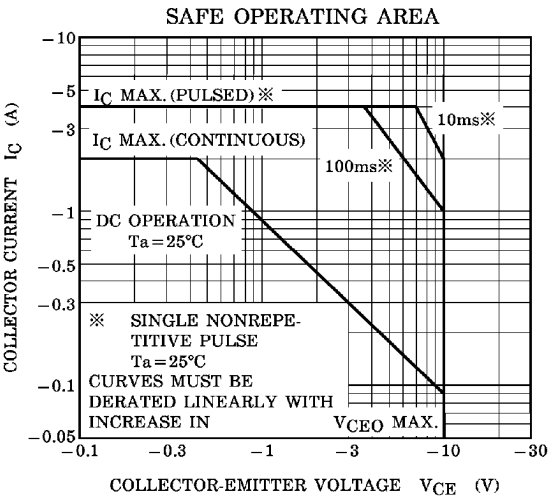
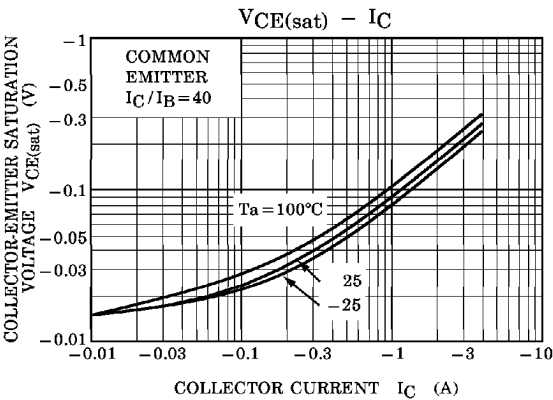
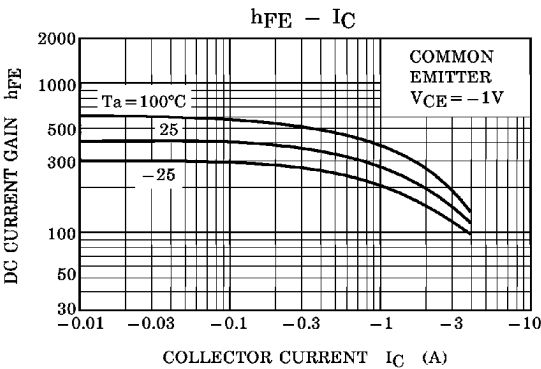
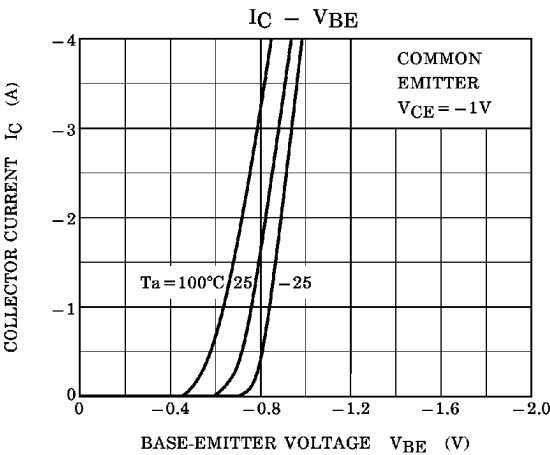
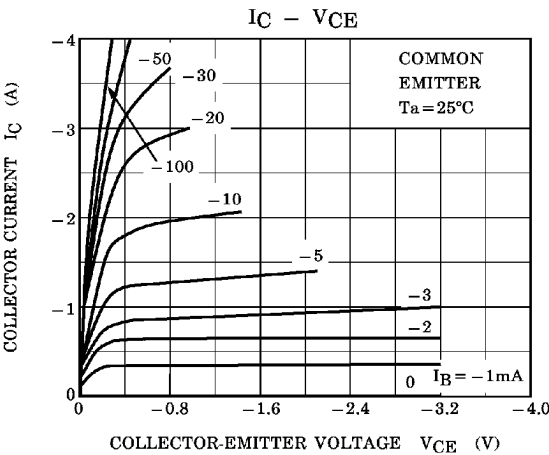
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -20V$ , $I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -6V$ , $I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA$ , $I_B = 0$	-10	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA$ , $I_C = 0$	-6	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note 2)	$V_{CE} = -1V$ , $I_C = -0.5A$	140	—	600	
	$h_{FE(2)}$	$V_{CE} = -1V$ , $I_C = -4A$	60	120	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A$ , $I_B = -50mA$	—	-0.20	-0.50	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -1V$ , $I_C = -2A$	—	-0.83	-1.5	V
Transition Frequency	$f_T$	$V_{CE} = -1V$ , $I_C = -0.5A$	—	140	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V$ , $I_E = 0$ , $f = 1MHz$	—	50	—	pF

Note 2 :  $h_{FE(1)}$  Classification    A : 140~280, B : 200~400, C : 300~600

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